

IN THE CLAIMS

Claims 1 - 16 (Cancelled)

17. (Currently Amended) An integrated circuit (IC) comprising:
a substrate comprising at least one level of interconnection;
an insulating layer formed directly on a surface of the substrate;
at least one ~~conductive structure~~bond pad formed directly on the insulating layer, the ~~conductive structure comprising a contact~~at least one bond pad coupled through the insulating layer to the at least one level of interconnection of the substrate;
an adhesion layer formed on a ~~top~~ surface of ~~said the~~ insulating layer such that the insulating layer is disposed between the adhesion layer and the substrate; and
a ~~first~~ passivation layer formed on a ~~top~~ surface of said adhesion layer and a ~~top portion~~ of a surface of the ~~conductive structure~~ bond pad that is less than the entire surface.
18. (Currently Amended) The integrated circuit of claim 17, wherein the passivation layer is a first passivation layer, the integrated circuit further comprising a second passivation layer formed upon said first passivation layer.
19. (Currently Amended) The integrated circuit of claim 17, wherein said insulating layer comprises an oxide layer comprising silicon dioxide (SiO_2).
20. (Currently Amended) The integrated circuit of claim 17, wherein said adhesion layer includes silicon oxynitride.
21. (Currently Amended) The integrated circuit of claim 17, wherein said ~~first~~ passivation layer includes silicon nitride (Si_3N_4).
22. (Currently Amended) The integrated circuit of claim 18, wherein said second passivation layer includes polyimide.
23. (Withdrawn) An integrated circuit comprising in a four layer stack:
a silicon dioxide insulating layer;

a silicon oxynitride adhesion layer formed on a surface of said silicon dioxide insulating layer by treating said surface of said silicon dioxide insulating layer with a gas;

a silicon nitride hard passivation layer formed directly on a surface of said silicon oxynitride adhesion layer; and

a photodefinable polyimide soft passivation layer formed on said silicon nitride hard passivation layer.

24. (Cancelled)

25. (Withdrawn) The integrated circuit of claim 17, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

26. (Withdrawn) The integrated circuit of claim 23, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH₃), oxygen and argon (Ar) and ozone (O₃) and argon.

27. (Currently Amended) An integrated circuit comprising:

a substrate;

an insulating layer formed on the substrate;

at least one ~~conductive structure~~bond pad formed directly on the insulating layer;

a composite film comprising:

a first layer ~~formed from a modification of a portion of the insulating layer~~, and

a second layer of a material different than a material of the first layer,

wherein the first layer is disposed between the insulating layer and the second layer, ~~and~~

wherein the first layer and the second layer comprise one common chemical element other than silicon; ~~and~~

wherein the second layer is a passivation layer formed on the first layer and a portion of a surface of the bond pad that is less than the entire surface.

28. (Currently Amended) The integrated circuit of claim 27, wherein said first layer includes silicon oxynitride.

29. (Currently Amended) The integrated circuit of claim ~~27~~28, wherein said second layer includes silicon nitride (Si_3N_4).